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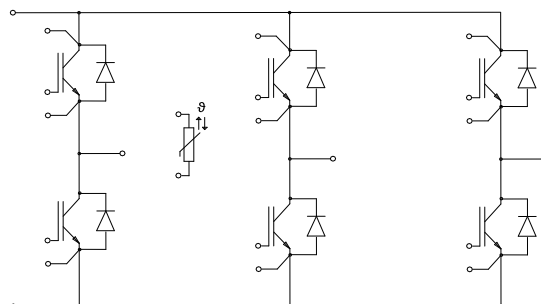
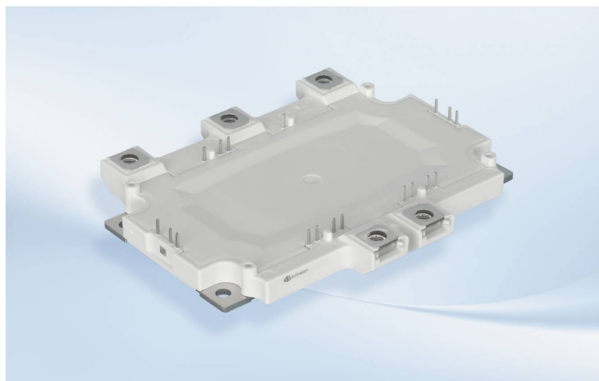
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HybridPACK™1 Modul mit Trench/Feldstopp IGBT3 und Emitter Controlled HE Diode und NTC
HybridPACK™1 module with Trench/Fieldstop IGBT3 and Emitter Controlled HE diode and NTC



$V_{CES} = 400V$
 $I_{C\ nom} = 215A / I_{CRM} = 430A$

Typische Anwendungen

- Anwendungen im Automobil
- Hybrid-Elektrofahrzeuge (H)EV
- Hybrid-Nutzfahrzeuge
- Motorantriebe

Typical Applications

- Automotive Applications
- Hybrid Electrical Vehicles (H)EV
- Commercial Agriculture Vehicles
- Motor Drives

Elektrische Eigenschaften

- Niedrige Schaltverluste
- Niedriges V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$
- Trench IGBT 3
- V_{CEsat} mit positivem Temperaturkoeffizienten
- Verstärkte Diode für Rückspeisebetrieb

Electrical Features

- Low Switching Losses
- Low V_{CEsat}
- $T_{vj\ op} = 150^{\circ}C$
- Trench IGBT 3
- V_{CEsat} with positive Temperature Coefficient
- Enlarged Diode for regenerative operation

Mechanische Eigenschaften

- 2,5 kV AC 1min Isolationsfestigkeit
- Al_2O_3 Substrat mit kleinem thermischen Widerstand
- Hohe mechanische Robustheit
- Integrierter NTC Temperatur Sensor
- Kupferbodenplatte
- RoHS konform
- Standardgehäuse

Mechanical Features

- 2.5 kV AC 1min Insulation
- Al_2O_3 Substrate with Low Thermal Resistance
- High mechanical robustness
- Integrated NTC temperature sensor
- Copper Base Plate
- RoHS compliant
- Standard Housing

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

| Content of the Code | Digit |
|----------------------------|---------|
| Module Serial Number | 1 - 5 |
| Module Material Number | 6 - 11 |
| Production Order Number | 12 - 19 |
| Datecode (Production Year) | 20 - 21 |
| Datecode (Production Week) | 22 - 23 |

| | | |
|-----------------|---------------------------------|----------------------|
| prepared by: WJ | date of publication: 2014-05-15 | |
| approved by: LB | revision: 3.0 | UL approved (E83335) |

IGBT, Wechselrichter / IGBT, Inverter
Höchstzulässige Werte / Maximum Rated Values

| | | | | |
|--|--|----------------------------|------------|--------|
| Kollektor-Emitter-Sperrspannung Collector-emitter voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{CES} | 400 | V |
| Kollektor-Dauergleichstrom Continuous DC collector current | $T_C = 85^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | $I_{C\text{nom}}$ I_C | 215 290 | A A |
| Periodischer Kollektor-Spitzenstrom Repetitive peak collector current | $t_P = 1\text{ ms}$ | I_{CRM} | 430 | A |
| Gesamt-Verlustleistung Total power dissipation | $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 175^{\circ}\text{C}$ | P_{tot} | 715 | W |
| Gate-Emitter-Spitzenspannung Gate-emitter peak voltage | | V_{GES} | +/-20 | V |

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|---|---|---|--------------------|----------------------|------|---|
| Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage | $I_C = 215\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 215\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 215\text{ A}, V_{GE} = 15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | $V_{CE\text{sat}}$ | 1,30 1,40 1,45 | 1,70 | V V V |
| Gate-Schwellenspannung Gate threshold voltage | $I_C = 3,20\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$ | | V_{GEth} | 5,0 5,8 6,5 | | V |
| Gateladung Gate charge | $V_{GE} = -15\text{ V} \dots +15\text{ V}$ | | Q_G | 1,85 | | μC |
| Interner Gatewiderstand Internal gate resistor | $T_{vj} = 25^{\circ}\text{C}$ | | R_{Gint} | 1,0 | | Ω |
| Eingangskapazität Input capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{ies} | 12,5 | | nF |
| Rückwirkungskapazität Reverse transfer capacitance | $f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$ | | C_{res} | 0,45 | | nF |
| Kollektor-Emitter-Reststrom Collector-emitter cut-off current | $V_{CE} = 400\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{CES} | | 1,0 | mA |
| Gate-Emitter-Reststrom Gate-emitter leakage current | $V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$ | | I_{GES} | | 400 | nA |
| Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{don} | 0,06 0,07 0,07 | | μs μs μs |
| Anstiegszeit, induktive Last Rise time, inductive load | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_r | 0,07 0,08 0,08 | | μs μs μs |
| Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_{doff} | 0,25 0,27 0,28 | | μs μs μs |
| Fallzeit, induktive Last Fall time, inductive load | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | t_f | 0,04 0,06 0,06 | | μs μs μs |
| Einschaltverlustenergie pro Puls Turn-on energy loss per pulse | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 2100\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{on} | 0,35 0,55 0,65 | | mJ mJ mJ |
| Abschaltverlustenergie pro Puls Turn-off energy loss per pulse | $I_C = 215\text{ A}, V_{CE} = 120\text{ V}, L_S = 25\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 1200\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,8\ \Omega$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{off} | 3,00 3,65 3,75 | | mJ mJ mJ |
| Kurzschlußverhalten SC data | $V_{GE} \leq 15\text{ V}, V_{CC} = 200\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ | $t_P \leq 8\ \mu\text{s}, T_{vj} = 25^{\circ}\text{C}$ $t_P \leq 6\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$ | I_{SC} | 1600 1300 | | A A |
| Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case | pro IGBT / per IGBT | | R_{thJC} | | 0,21 | K/W |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 0,085 | | K/W |
| Temperatur im Schaltbetrieb Temperature under switching conditions | | | $T_{vj\text{op}}$ | -40 | 150 | $^{\circ}\text{C}$ |

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|-----------------|---------------------------------|
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Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

| | | | | |
|---|--|-----------|--------------|--|
| Periodische Spitzensperrspannung Repetitive peak reverse voltage | $T_{vj} = 25^{\circ}\text{C}$ | V_{RRM} | 400 | V |
| Dauergleichstrom Continuous DC forward current | | I_F | 430 | A |
| Periodischer Spitzenstrom Repetitive peak forward current | $t_P = 1\text{ ms}$ | I_{FRM} | 860 | A |
| Grenzlastintegral I^2t - value | $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$ | I^2t | 4600 4200 | A^2s A^2s |

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|---|--|---|--------------------|----------------------|------|---|
| Durchlassspannung Forward voltage | $I_F = 430\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 430\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 430\text{ A}, V_{GE} = 0\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | V_F | 1,35 1,25 1,20 | 1,75 | V V V |
| Rückstromspitze Peak reverse recovery current | $I_F = 430\text{ A}, -di_F/dt = 2100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 120\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | I_{RM} | 110 150 160 | | A A A |
| Sperrverzögerungsladung Recovered charge | $I_F = 430\text{ A}, -di_F/dt = 2100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 120\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | Q_r | 8,00 18,0 21,0 | | μC μC μC |
| Abschaltenergie pro Puls Reverse recovery energy | $I_F = 430\text{ A}, -di_F/dt = 2100\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 120\text{ V}$ $V_{GE} = -15\text{ V}$ | $T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$ | E_{rec} | 1,00 2,00 2,30 | | mJ mJ mJ |
| Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case | pro Diode / per diode | | R_{thJC} | | 0,23 | K/W |
| Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink | pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$ | | R_{thCH} | 0,085 | | K/W |
| Temperatur im Schaltbetrieb Temperature under switching conditions | | | $T_{vj\text{ op}}$ | -40 | 150 | $^{\circ}\text{C}$ |

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

| | | | min. | typ. | max. | |
|--|---|--|--------------|------|------|------------------|
| Nennwiderstand Rated resistance | $T_C = 25^{\circ}\text{C}$ | | R_{25} | 5,00 | | $\text{k}\Omega$ |
| Abweichung von R100 Deviation of R100 | $T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$ | | $\Delta R/R$ | -5 | 5 | % |
| Verlustleistung Power dissipation | $T_C = 25^{\circ}\text{C}$ | | P_{25} | | 20,0 | mW |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/50}$ | 3375 | | K |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/80}$ | 3411 | | K |
| B-Wert B-value | $R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$ | | $B_{25/100}$ | 3433 | | K |

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

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Modul / Module

| | | | | | |
|---|--|---------------------|--------------------------------|------|---------|
| Isolations-Prüfspannung Isolation test voltage | RMS, f = 50 Hz, t = 1 min. | V _{ISOL} | 2,5 | | kV |
| Material Modulgrundplatte Material of module baseplate | | | Cu | | |
| Innere Isolation Internal isolation | Basisisolation (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140) | | Al ₂ O ₃ | | |
| Kriechstrecke Creepage distance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 12,0 6,1 | | mm |
| Luftstrecke Clearance | Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal | | 12,0 6,1 | | mm |
| Vergleichszahl der Kriechwegbildung Comperative tracking index | | CTI | > 200 | | |
| | | | min. | typ. | max. |
| Modulstreuintduktivität Stray inductance module | | L _{sCE} | | 30 | nH |
| Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip | T _C = 25°C, pro Schalter / per switch | R _{CC+EE'} | | 1,00 | mΩ |
| Lagertemperatur Storage temperature | | T _{stg} | -40 | | 125 °C |
| Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting | Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note | M | 3,00 | - | 6,00 Nm |
| Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque | Schraube M6 - Montage gem. gültiger Applikationsschrift Screw M6 - Mounting according to valid application note | M | 3,0 | - | 6,0 Nm |
| Gewicht Weight | | G | | 485 | g |

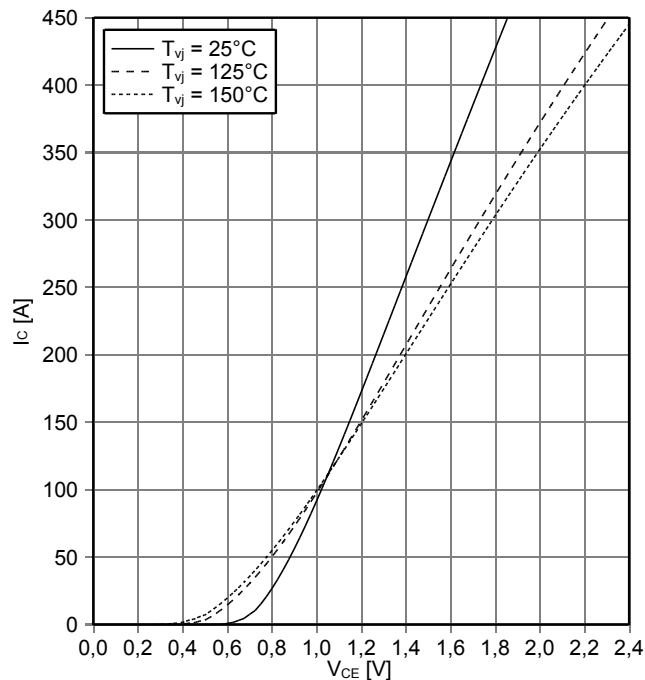
Der Kollektor-Dauergleichstrom / Dioden-Dauergleichstrom ist durch die Lastanschlüsse begrenzt.
DC-collector current / diode forward current limited by power terminals.

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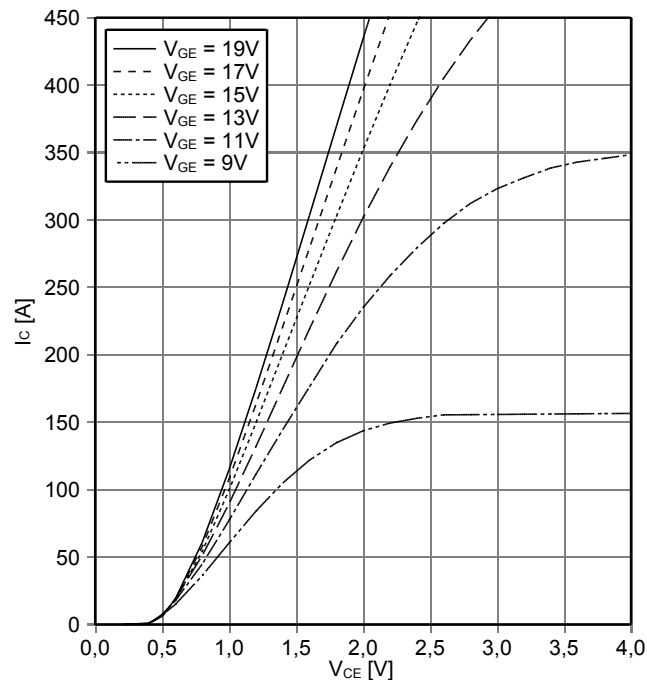
Ausgangskennlinie IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



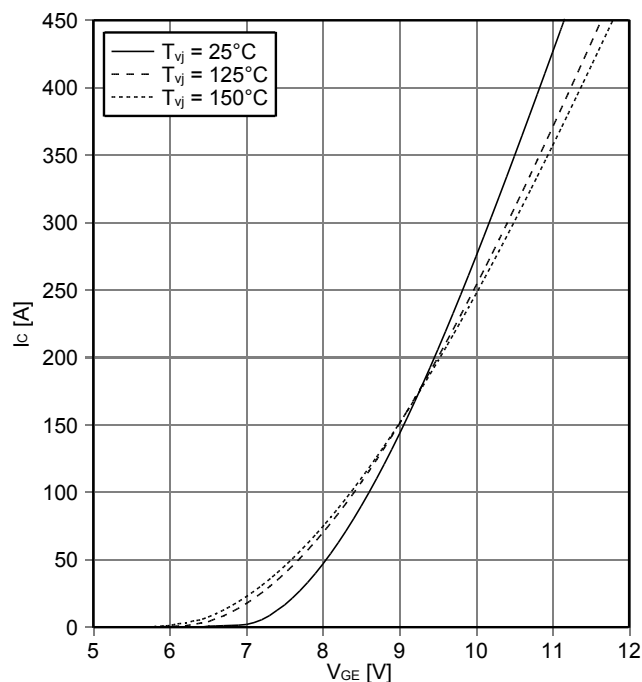
Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)
output characteristic IGBT, Inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



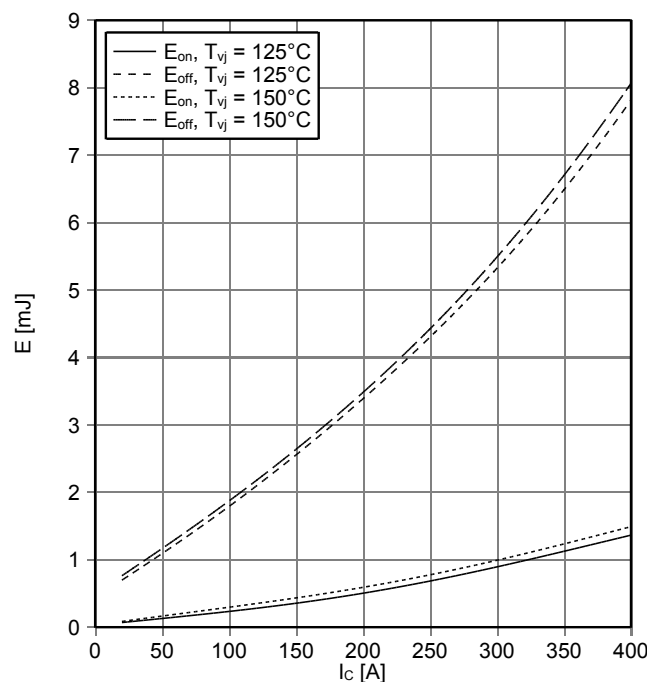
Übertragungscharakteristik IGBT, Wechselrichter (typisch)
transfer characteristic IGBT, Inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

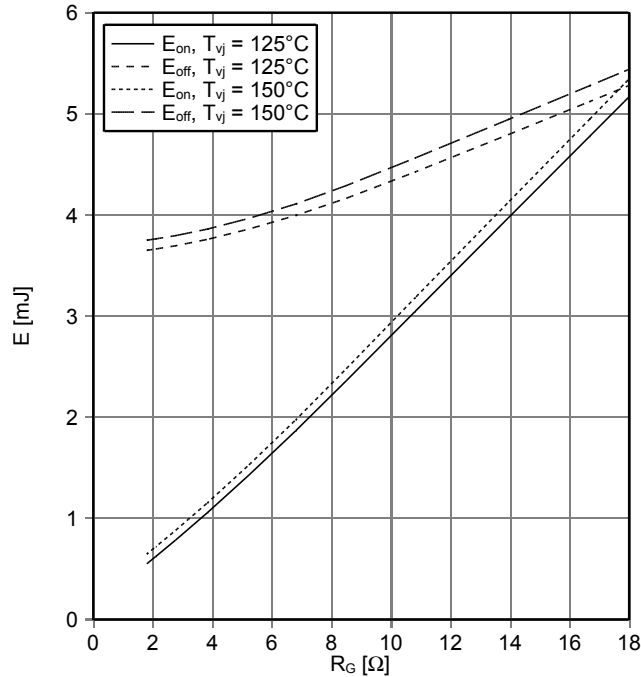
$E_{on} = f(I_C), E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 1.8\ \Omega, R_{Goff} = 1.8\ \Omega, V_{CE} = 120\text{ V}$



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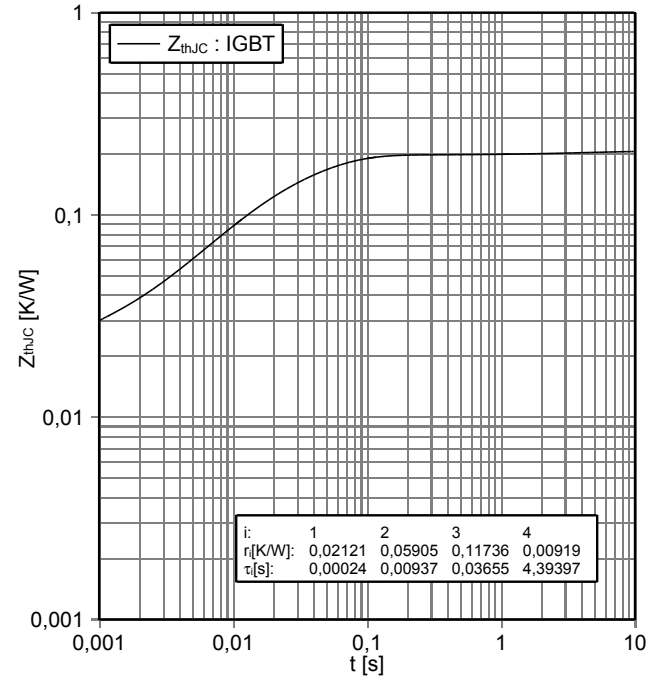
Schaltverluste IGBT, Wechselrichter (typisch)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G), E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}, I_C = 215 \text{ A}, V_{CE} = 120 \text{ V}$



Transienter Wärmewiderstand IGBT, Wechselrichter
transient thermal impedance IGBT, Inverter

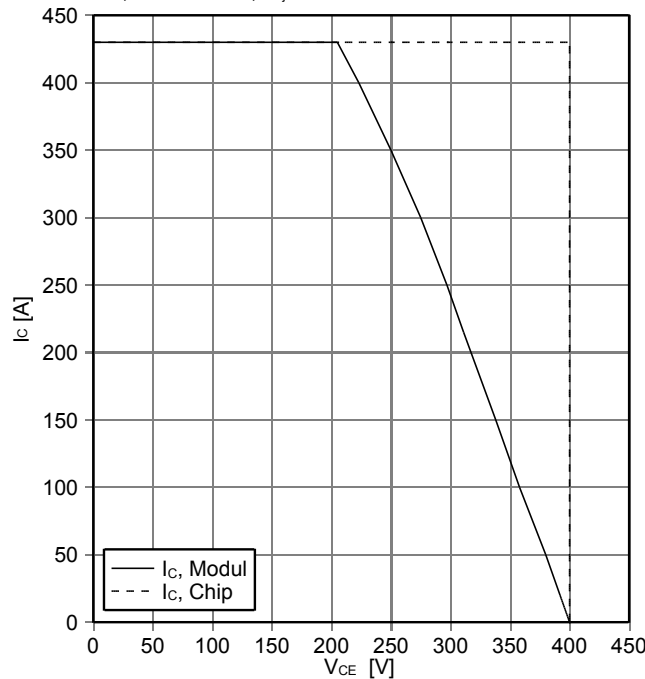
$Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter
(RBSOA)

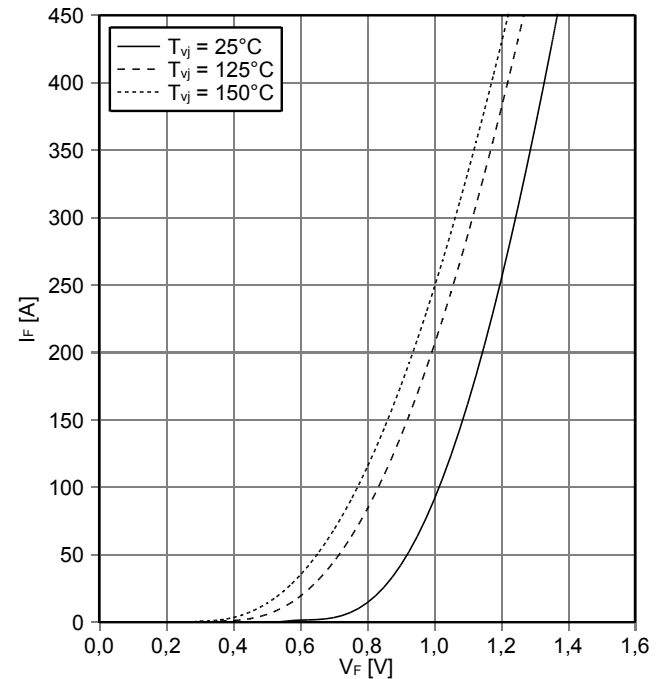
reverse bias safe operating area IGBT, Inverter (RBSOA)

$I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.8 \Omega, T_{vj} = 150^\circ\text{C}$



Durchlasskennlinie der Diode, Wechselrichter (typisch)
forward characteristic of Diode, Inverter (typical)

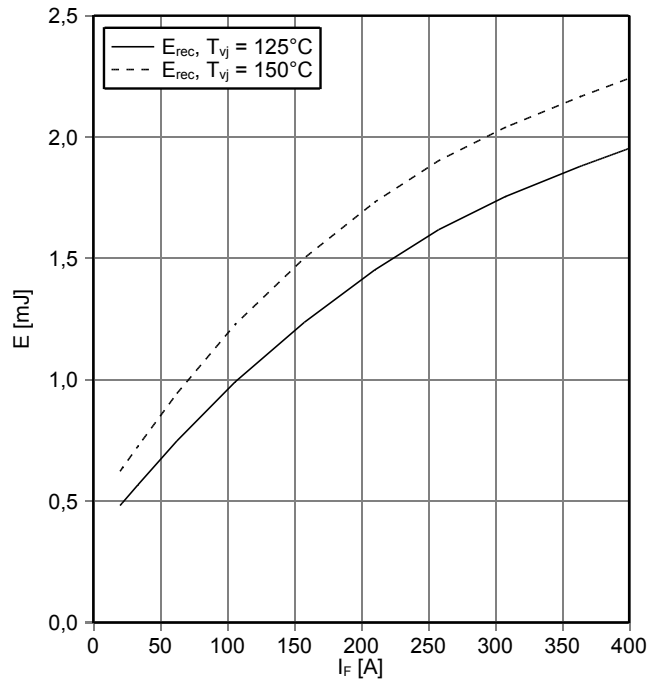
$I_F = f(V_F)$



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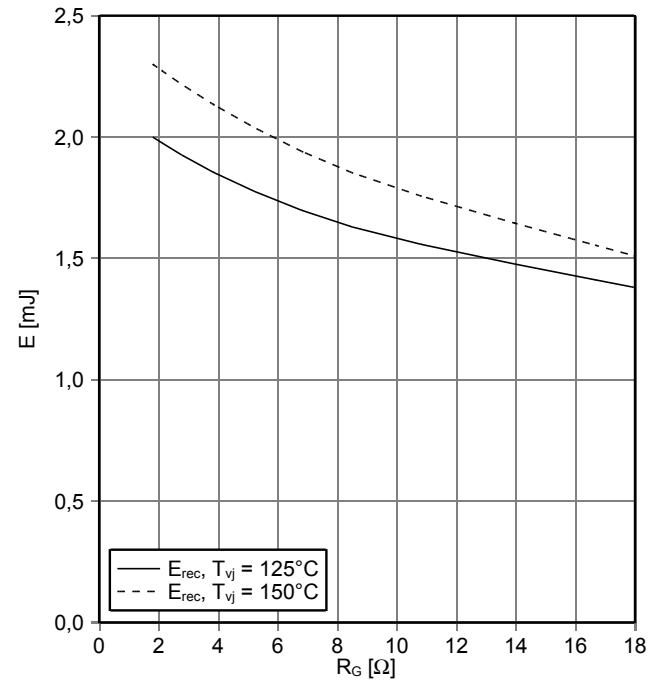
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 1.8 \Omega, V_{CE} = 120 V$



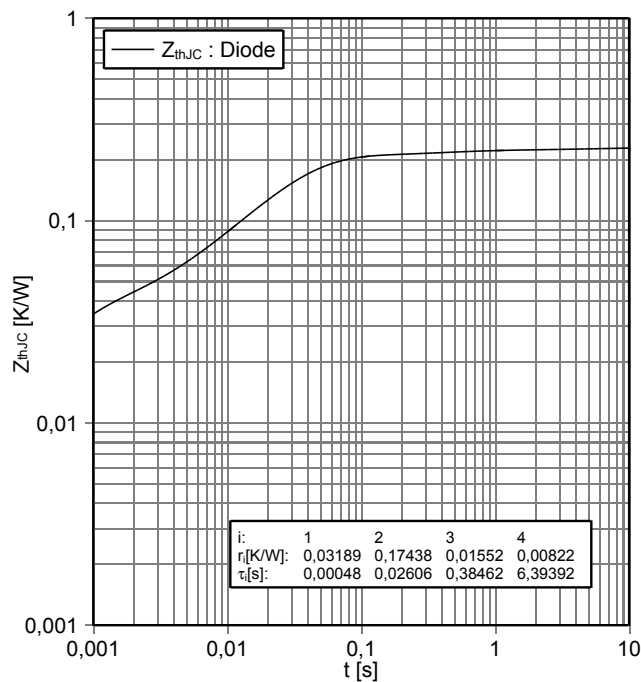
Schaltverluste Diode, Wechselrichter (typisch)
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 430 A, V_{CE} = 120 V$



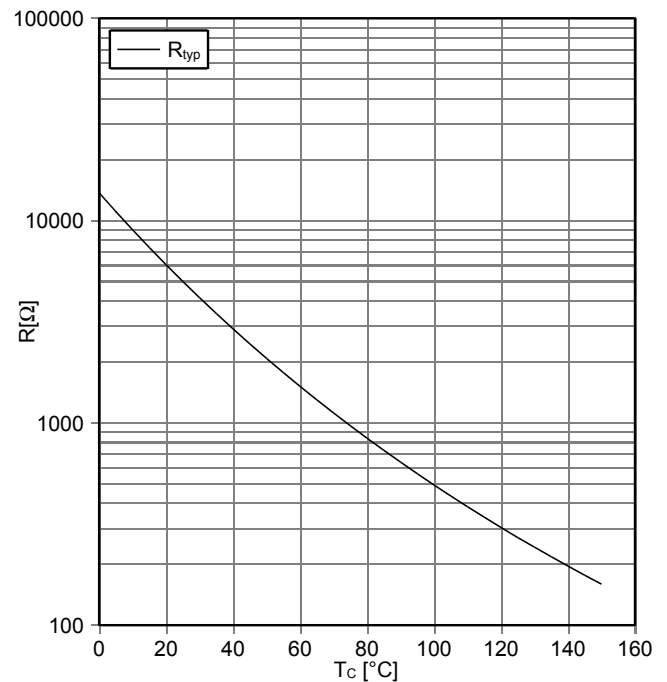
Transienter Wärmewiderstand Diode, Wechselrichter
transient thermal impedance Diode, Inverter

$Z_{thJC} = f(t)$



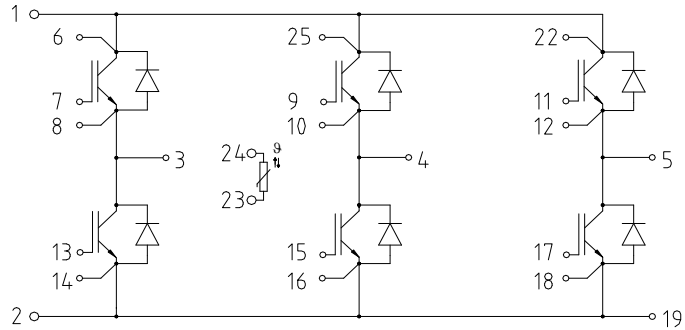
NTC-Widerstand-Temperaturkennlinie (typisch)
NTC-Thermistor-temperature characteristic (typical)

$R = f(T)$

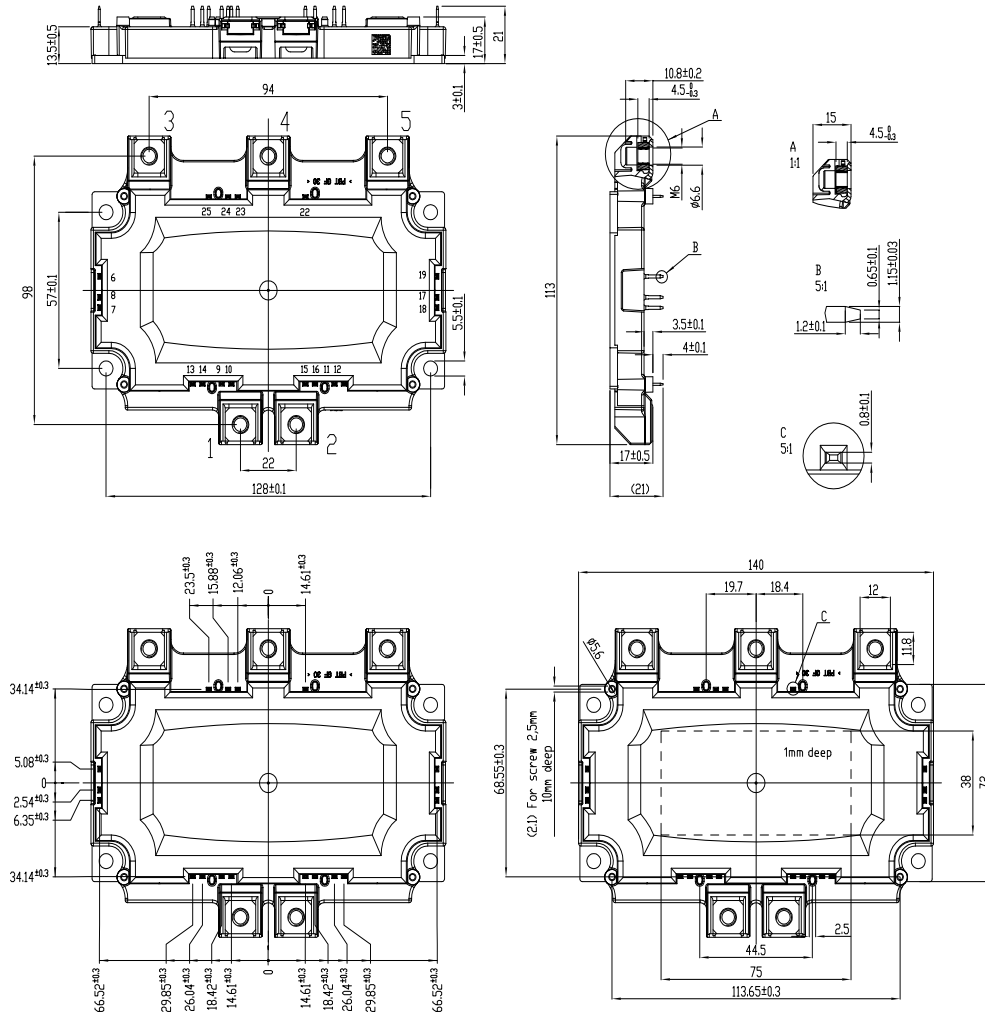


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Schaltplan / circuit_diagram_headline



Gehäuseabmessungen / package outlines



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Sollten Sie von uns Produktinformationen benötigen, die über den Inhalt dieses Produktdatenblatts hinausgehen und insbesondere eine spezifische Verwendung und den Einsatz dieses Produktes betreffen, setzen Sie sich bitte mit dem für Sie zuständigen Vertriebsbüro in Verbindung (siehe www.infineon.com, Vertrieb&Kontakt). Für Interessenten halten wir Application Notes bereit.

Aufgrund der technischen Anforderungen könnte unser Produkt gesundheitsgefährdende Substanzen enthalten. Bei Rückfragen zu den in diesem Produkt jeweils enthaltenen Substanzen setzen Sie sich bitte ebenfalls mit dem für Sie zuständigen Vertriebsbüro in Verbindung.

Sollten Sie beabsichtigen, das Produkt in Anwendungen der Luftfahrt, in gesundheits- oder lebensgefährdenden oder lebenserhaltenden Anwendungsbereichen einzusetzen, bitten wir um Mitteilung. Wir weisen darauf hin, dass wir für diese Fälle

- die gemeinsame Durchführung eines Risiko- und Qualitätsassessments;
- den Abschluss von speziellen Qualitätssicherungsvereinbarungen;
- die gemeinsame Einführung von Maßnahmen zu einer laufenden Produktbeobachtung dringend empfehlen und gegebenenfalls die Belieferung von der Umsetzung solcher Maßnahmen abhängig machen.

Soweit erforderlich, bitten wir Sie, entsprechende Hinweise an Ihre Kunden zu geben.

Inhaltliche Änderungen dieses Produktdatenblatts bleiben vorbehalten.

Terms & Conditions of usage

The data contained in this product data sheet is exclusively intended for technically trained staff. You and your technical departments will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to such application.

This product data sheet is describing the characteristics of this product for which a warranty is granted. Any such warranty is granted exclusively pursuant the terms and conditions of the supply agreement. There will be no guarantee of any kind for the product and its characteristics. The information in the valid application- and assembly notes of the module must be considered.

Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you (see www.infineon.com). For those that are specifically interested we may provide application notes.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the Product in aviation applications, in health or live endangering or life support applications, please notify. Please note, that for any such applications we urgently recommend

- to perform joint Risk and Quality Assessments;
- the conclusion of Quality Agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery depended on the realization of any such measures.

If and to the extent necessary, please forward equivalent notices to your customers.

Changes of this product data sheet are reserved.

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